

FORM PTO-1449	SERIAL NO. 10/667,707	CASE NO. 9905/35
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)	FILING DATE September 22, 2003	GROUP ART UNIT 1765
APPLICANT(S): Moriceau et al.		

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER Number-Kind Code (If known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
SA	C74 WO 2004/044976	5/27/2004	WIPO		Abstract

EXAMINER INITIAL	OTHER ART - NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)				
	C75	Agarwal et al "Efficient production of Silicon-on-insulator films by co-implatation of HE <sup>+</sup> with H <sup>-</sup> , <i>Applied Physics Letter, American Institute of Physics</i> , Vol. 72, No. 9, March 1998, pp. 1086-1088			
	C76	Bruel et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington			
	C77	Camperi-Gimelset et al., "Alignable Epitaxial Lift-off of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126			
	C78	Cerofolini et al. "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 198-202			
	C79	Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135			
	C80	DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa. 200460411			
	C81	Feijoo et al., "Prestressing of Bonded Wafers" Vol. 92-7 1992 pp. 230-238			
	C82	Feng et al., "Generalized Formula for Curvature Radius and Layer Stresses Caused by Thermal Strain in Semiconductor Multilayer Structures", <i>J. Appl. Phys.</i> , Vol. 54, No. 1, 1983, pp. 83-85			
	C83	Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691			
	C84	Henttinen et al. "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372			
	C85	Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107			
	C86	Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 37, No. 4, 1988, pp. 2530-2535			
	C87	Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.			
	C88	Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062			

EXAMINER /Shamim Ahmed/ (01/24/2007)	DATE CONSIDERED 01/24/2007
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.